

ABSTRACT

COMPOSITION AND PROCESS FOR SELECTIVELY ETCHING METAL NITRIDES

A removal composition and process for selectively removing a first metal gate material (e.g., titanium nitride) relative to a second metal gate material (e.g., tantalum nitride) from a microelectronic device having said material thereon. The removal composition can include fluoride or alternatively be substantially devoid of fluoride. The substrate preferably comprises a high-k/metal gate integration scheme.

(No Suitable Figure)